Application No.: 10/734,201 Docket No.: M4065.0489/P489-A

AMENDMENTS TO THE CLAIMS

- 1-21. (Cancelled)
- 22. (Currently Amended) A magnetic random access memory structure comprising:

a plurality of longitudinally extending planarized conductive lines formed over an insulating layer of a semiconductor substrate;

respective first magnetic layers over said conductive lines;

respective second magnetic layers over said first magnetic layers;

at least one contact; and

a planarized conductive material layer formed between said planarized conductive lines and said first magnetic layers.

- 23. (Currently Amended) The structure of claim 22 wherein said conductive material layer is selected from the group consisting of tantalum (Ta), titanium (Ti), titanium-tungsten (TiW), titanium nitride (TiN) and chromium (Cr).
- 24. (Currently Amended) The structure of claim 22 wherein said conductive material layer is a resistive material.
- 25. (Original) The structure of claim 22 wherein said insulating layer is selected from the group consisting of BPSG, SiO₂, Si₃N₄ and polyimide.
- 26. (Currently Amended) The structure of claim 22 wherein said conductive material layer is formed to a thickness of about 5 nm to about 20 nm.

Application No.: 10/734,201 Docket No.: M4065.0489/P489-A

27. (Original) The structure of claim 22 wherein said conductive lines are formed in a trench formed in said substrate.

28. (Currently Amended) A memory device comprising:

at least one magnetic random access memory cell, said magnetic random access memory cell comprising a first ferromagnetic layer formed over a first planarized conductor, a second ferromagnetic layer formed over said first ferromagnetic layer, a nonmagnetic layer between said first and second ferromagnetic layers, and a planarized conductor conductive material layer provided between said first conductor and said first ferromagnetic layer.

- 29. (Currently Amended) The device of claim 28 wherein said conductive material layer is selected from the group consisting of tantalum (Ta), titanium (Ti), titanium-tungsten (TiW), titanium nitride (TiN) and chromium (Cr).
- 30. (Currently Amended) The device of claim 28 wherein said conductive material layer is a resistive material.
- 31. (Original) The device of claim 28 wherein said insulating layer is selected from the group consisting of BPSG, SiO, SiO₂, Si₃N₄ or polyimide.
- 32. (Currently Amended) The device of claim 28 wherein said conductive material layer is formed to a thickness of about 5 nm to about 20 nm.
- 33. (Currently Amended) The device of claim 28 wherein said <u>planarized</u> first conductor is formed in a trench of a substrate.
 - 34. 39. (Canceled)